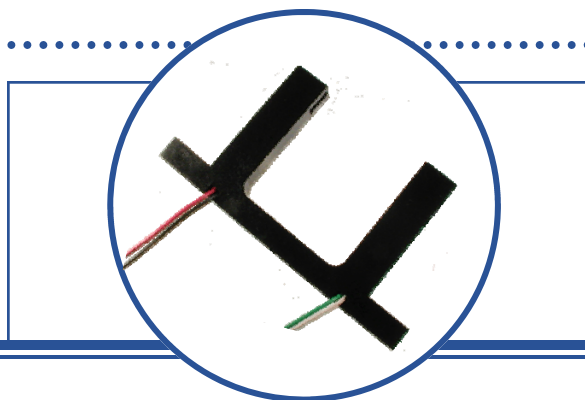


Slotted Optical Switch OPB819Z



Features:

- Non-contact switching
- 24" (609 mm) long wire leads
- 1.25" (31.75 mm) wide slot, 1.38" (35.05 mm) deep slot



Description:

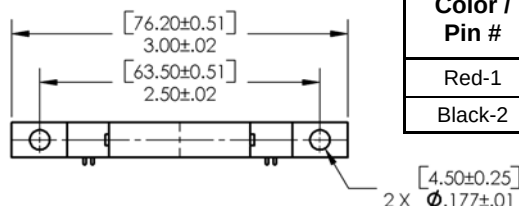
The **OPB819Z** slotted switch consists of an infrared emitting diode and an NPN silicon phototransistor mounted in an opaque housing with clear windows for dust protection. Switching of the phototransistor occurs whenever an opaque object passes through the slot.

The **OPB819Z** has an 1.38" (35.05 mm) deep and 1.25" (31.75 mm) wide slot allowing for a longer reach of the optical center line from the mounting plane. The switch housing is designed to use the lens of each component as the optical aperture resulting in an equivalent aperture diameter of 0.06" (1.52 mm).

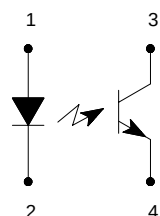
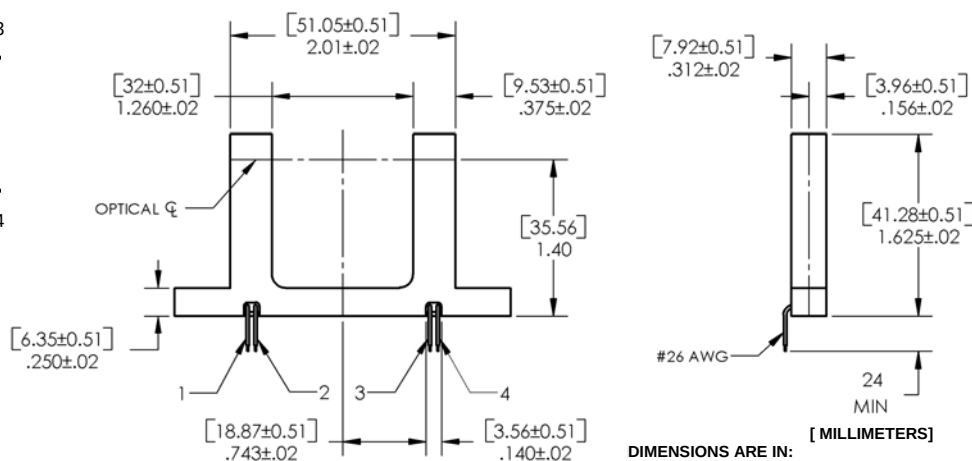
Custom electrical, wire and cabling and connectors are available. Contact your local representative or OPTEK for more information.

Applications:

- Non-contact object sensing
- Assembly line automation
- Machine automation
- Equipment security
- Machine safety



Color / Pin #	Description	Color / Pin #	Description
Red-1	Anode	White-3	Collector
Black-2	Cathode	Green-4	Emitter



DIMENSIONS ARE IN:
[MILLIMETERS]
INCHES

Ordering Information					
Part Number	LED Peak Wavelength	Sensor	Slot Width / Depth	Aperture Emitter/ Sensor	Lead Length / Spacing
OPB819Z	890 nm	Transistor	1.26" / 1.38"	None	24" / 26 AWG Wire



RoHS

OPTEK reserves the right to make changes at any time in order to improve design and to supply the best product possible.

CONTAINS POLYSULFONE
To avoid stress cracking, we suggest using ND Industries' **Vibra-Tite** for thread-locking. **Vibra-Tite** evaporates fast without causing structural failure in OPTEK's molded plastics.

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Storage & Operating Temperature Range	-40° C to +85° C
Lead Soldering Temperature [1/16 inch (1.6mm) from the case for 5 sec. with soldering iron] ⁽¹⁾	260° C

Input Diode

Forward DC Current	50 mA
Peak Forward Current (1 μs pulse width, 300 pps)	3 A
Reverse DC Voltage	2 V
Power Dissipation ⁽²⁾	100 mW

Output Phototransistor

Collector-Emitter Voltage	30 V
Emitter-Collector Voltage	5 V
Collector DC Current	30 mA
Power Dissipation ⁽²⁾	100 mW

Electrical Characteristics ($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
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Input Diode

V_F	Forward Voltage	-	-	1.8	V	$I_F = 20 \text{ mA}$
I_R	Reverse Current	-	-	100	μA	$V_R = 2.0 \text{ V}$

Output Phototransistor

$V_{(BR)(CEO)}$	Collector-Emitter Breakdown Voltage	30	-	-	V	$I_C = 100 \mu\text{A}$, $I_F = 0$, $E_E = 0$
$V_{(BR)(ECO)}$	Emitter-Collector Breakdown Voltage	5	-	-	V	$I_E = 100 \mu\text{A}$, $I_F = 0$, $E_E = 0$
I_{CEO}	Collector-Emitter Leakage Current	-	-	100	nA	$V_{CE} = 10 \text{ V}$, $I_F = 0$, $E_E = 0$

Coupled

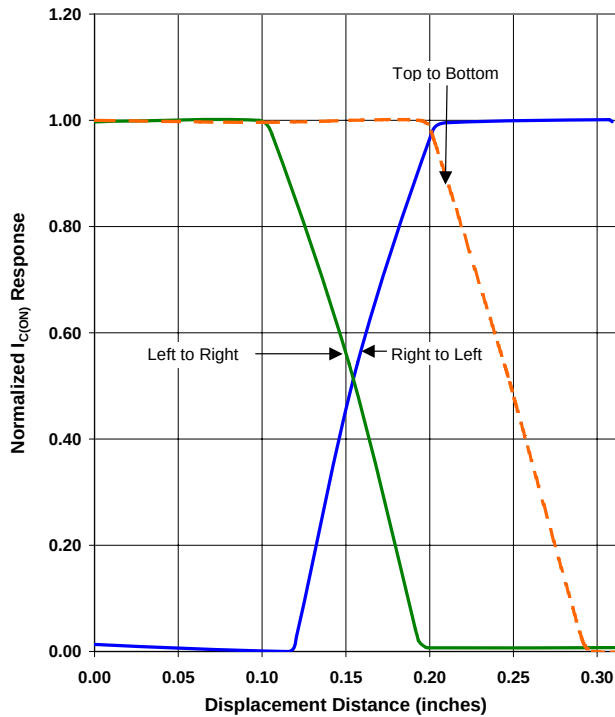
$I_{C(ON)}$	On-State Collector Current	0.5	-	12.0	mA	$V_{CE} = 5 \text{ V}$, $I_F = 40 \text{ mA}$
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage	-	-	0.4	V	$I_C = 250 \mu\text{A}$, $I_F = 40 \text{ mA}$

Notes:

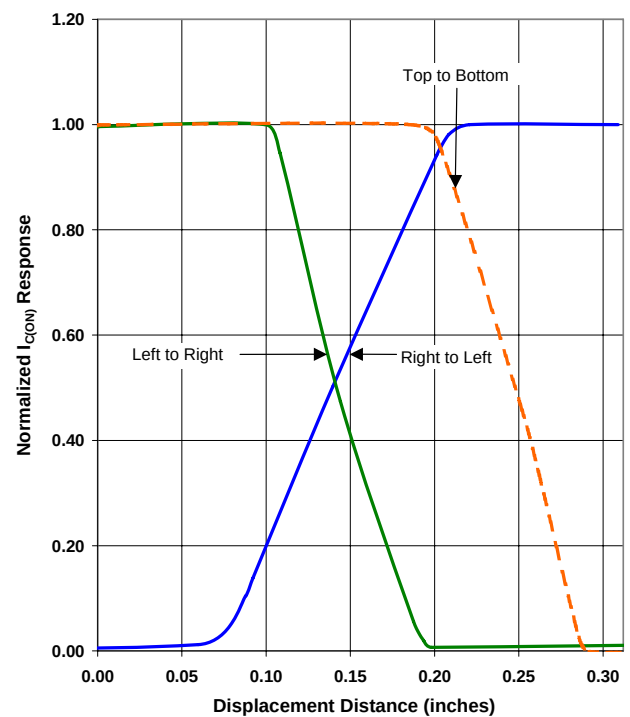
- (1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- (2) Derate linearly 1.67 mW/°C above 25° C.
- (3) All parameters tested using pulse techniques.
- (4) Methanol or isopropanol are recommended as cleaning agents. Plastic housing is soluble in chlorinated hydrocarbons and ketones. Spray and wipe. Do not submerge.
- (5) Polarity is denoted by color the wires: LED (Anode—Red, Cathode—Black); Phototransistor (Collector—White, Emitter—Green).

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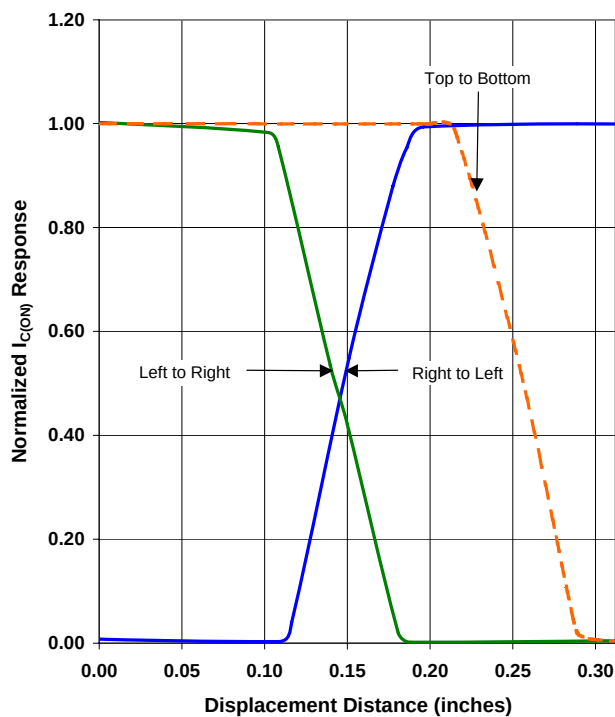
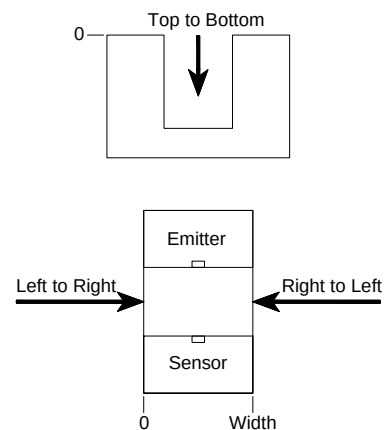
OPB819 - Flag Next to Emitter



OPB819 - Flag Next to Sensor



OPB819 - Flag in Middle of Slot



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